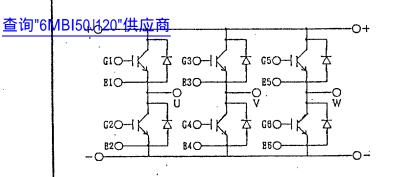
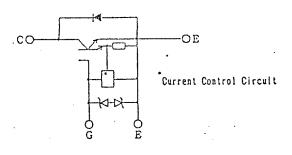


2. Equivalent Circuit of Module

3. Equivalent Circuit





4. Absolute Maximum Ratings (Tj=25°C)

Items		Symbols	Ratings	Units	
Collector-emi	tter voltage	Vces	1 2 0 0	٧	
Gate -emitter	Gate -cmitter voltage		± 2 0	γ	
Continuous		I c	5 0		
Collector	1 ms	I c pulse	1 0 0	А	
. current		- I c	5 0	A	
	1 ms	- I c pulse	1 0 0		
Max.power dis	Max.power dissipation		3 2 0	W	
Operating temperature		Tj	+150	°C	
Storage temperature		Tstg	-40~+125	·c	
Isolation voltage		Vis	AC 2500 (Inin)	Λ.	
Screw Torque		Mounting * 1	3. 5	N·m	
		Terminals * 2	1. 7	IA . Wr	

Note: \*1 Recommendable Value :  $2.5 \sim 3.5 \text{ N} \cdot \text{m}$  (M5) \*2 Recommendable Value :  $1.3 \sim 1.7 \text{ N} \cdot \text{m}$  (M4)

		:							
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5. Static electrical characteristics

( at Tj=25°C unless otherwise specified )

MBI50J120"供应商		<b>C</b> 1 1	Characteristics		Conditions		Units	
1	Items	Symbols	min.	typ.	max.	Conai	tions	Units
Zero	gate voltage				1.0	Tj= 25°C	V <sub>GE</sub> =0V	m A
colle	ctor current	ICES				Tj=125°C	V <sub>CE</sub> =1200V	m A
Gate-	emitter	•			15	V cE=	D V	μA
leakage current		I ees			15	V 6 E = 3	$_{GE} = \pm 20V$	
Gate-emitter threshold voltage						V c = 2	V cr=20V	
		V GE (th)		5.0	,,	Ic = 50mA		V
	ector-emitter	**		2.2		V G E = 1.5Y		v
Sâ	aturation voltage	V CE (sat)		4.4		I c = 5	I c = 50A	
6. Dyr	namic ratings	( at Tj=25	Char	acterist	ics		itions	Unit
			min.	typ.	max.		<u> </u>	<u> </u>
Inpu	t capacitance	Cles		6000		V <sub>GE</sub> =	0 V	
	t capacitance							
Outp	ut capacitance	Coes		_		V cr=	10V	p F

Items		Characteristics			C 41 bi	Units
	Symbols	min.	typ.	max.	Conditions	UIILS
Input capacitance	Cles		6000		V G E = 0 V	
Output capacitance	Coes		_		$V_{cE} = 10V$	рF
Reverse transfer capacitance	Cres		-		f = 1 MHz	
Turn-on time	t on		0.70		V <sub>cc</sub> =600Y	
	tr		0.30		$I_c = 50A$	μs
Turn-off time	toff		0.95		$V_{GE} = \pm 15V$ $R_G = 24\Omega$	μ 5
	t f		0.20			

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( at Tj=25°C unless otherwise specified ) 7. Characteristics of reverse diode

查询"(	查询"6MB[50J120"供应商			Characte		ics	Conditions	Units
		'Items	Symbols	min.	typ.	max.	Conditions	UIII
-	. D	Diode forward on-voltage	VF		2.5		IF = 50A V <sub>GE</sub> = 0V	V
	R	Reverse recovery time	trr			350	IF = 50A -di/dt=150A/μs	ns

8. Thermal resistance characteristics

Items		Characteristics			Condi <b>ti</b> ons	Units
	Symbols	min.	typ.	max.	conditions	
	Rth(j-c)			0.391	IGBT (MBT)	
Thermal resistance	Rth(j-c)		-	0.749	Diode	·c / W
	* R th (c-f)		0.05		the base to cooling fin	

This is the value which is defined mounting on the additional cooling fin Ж with thermal compound.

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